

1 is wider than an etched area at the lower end surfaces of the first and second dummy bridges.

2 [0018] Furthermore, an etched area at an upper surface above the first etching boundary of the first
3 dummy bridge is wider than an etched area at a lower surface therebelow, and an etched area at a
4 lower surface below the second etching boundary of the second dummy bridge is wider than an
5 etched area at an upper surface thereabove.

6 BRIEF DESCRIPTION OF THE DRAWINGS

7 [0019] A more complete appreciation of this invention, and many of the attendant advantages
8 thereof, will be readily apparent as the same becomes better understood by reference to the
9 following detailed description when considered in conjunction with the accompanying drawings in
10 which like reference symbols indicate the same or similar components, wherein:

11 [0020] FIG. 1 is a plan view of an earlier tension mask;

12 [0021] FIG. 2 is an enlarged plan view of the part A of FIG. 1;

13 [0022] FIG. 3 is a plan view of a slot in which an earlier dummy bridge is formed;

14 [0023] FIG. 4A is a sectional view taken along the line I-I of FIG. 3;

15 [0024] FIG. 4B is a sectional view taken along the line II-II of FIG. 3;

16 [0025] FIG. 5 is an sectional elevation view of a cathode ray tube according to an embodiment
17 of the present invention;

18 [0026] FIG. 6 is a perspective view of a tension mask assembly of FIG. 5;

19 [0027] FIG. 7 is an enlarged perspective view of the part B of FIG. 6;

20 [0028] FIG. 8 is a perspective view of a portion of a slot at which a dummy bridge shown in FIG.

7 is formed;

[0029] FIG. 9A is a sectional view taken along the line III-III of FIG. 8;

[0030] FIG. 9B is a sectional view taken along the line IV-IV of FIG. 8 and shows an etching step;

[0031] FIG. 9C is a sectional view taken along the line IV-IV of FIG. 8 and shows a state after the etching step according to a first embodiment of the present invention;

[0032] FIG. 9D is a sectional view taken along the line IV-IV of FIG. 8 and shows a state after the etching step according to a first embodiment of the present invention;

[0033] FIG. 10A is a sectional view of the part C of FIG. 6, taken along the line V-V, and shows a portion of a slot in which dummy bridges are formed;

[0034] FIG. 10B is a sectional view of the part D of FIG. 6, taken along the line V-V, and shows a portion of a slot in which dummy bridges are formed; and

[0035] FIG. 10C is a sectional view of the part E of FIG. 6, taken along the line V-V, and shows a portion of a slot in which dummy bridges are formed.

DETAILED DESCRIPTION OF THE PRESENT INVENTION

[0036] Turning now to the drawings, referring to FIGS. 1 and 2, the tension mask 10 includes a plurality of strips 12 formed on a metal foil 11 such that they are separated from one another at predetermined intervals, slots 13 intermittently formed between the strips 12 for allowing many electron beams to pass, real bridges 14 for supporting the slots 13, and dummy bridges 15 extending from the strips 12 to the slots 13. At least one dummy bridge 15 is formed for each slot 13.

[0037] FIG. 3 illustrates a slot 33 in which a dummy bridge 35 is formed. Referring to FIG. 3,